

XN1000~, XN2000~

2-Element Compound Transistor (MINI Type Package (5-pin))

■ Features

- Automatic soldering possible in both flow and re-flow directions
- Reduction in mounting area of 50% per device
- Packaging specifications (8mm taping, horizontal magazine) available, can be handled by automatic mounting machines
- Terminal width changed to 0.3mm from 0.4mm to prevent solder bridges

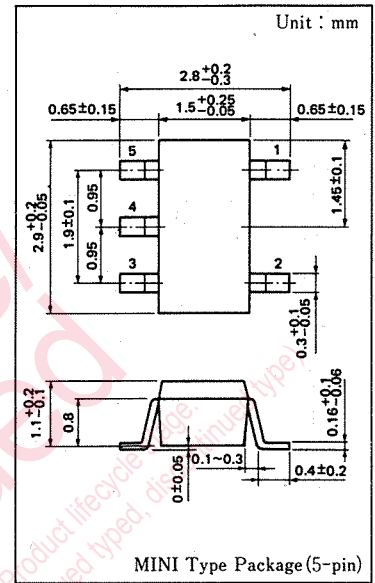
■ Standard Package criteria

Allowable Soldering Part Temperature	Storage Temperature	Power Dissipation
150°C	-55 ~ +150°C	300mW*

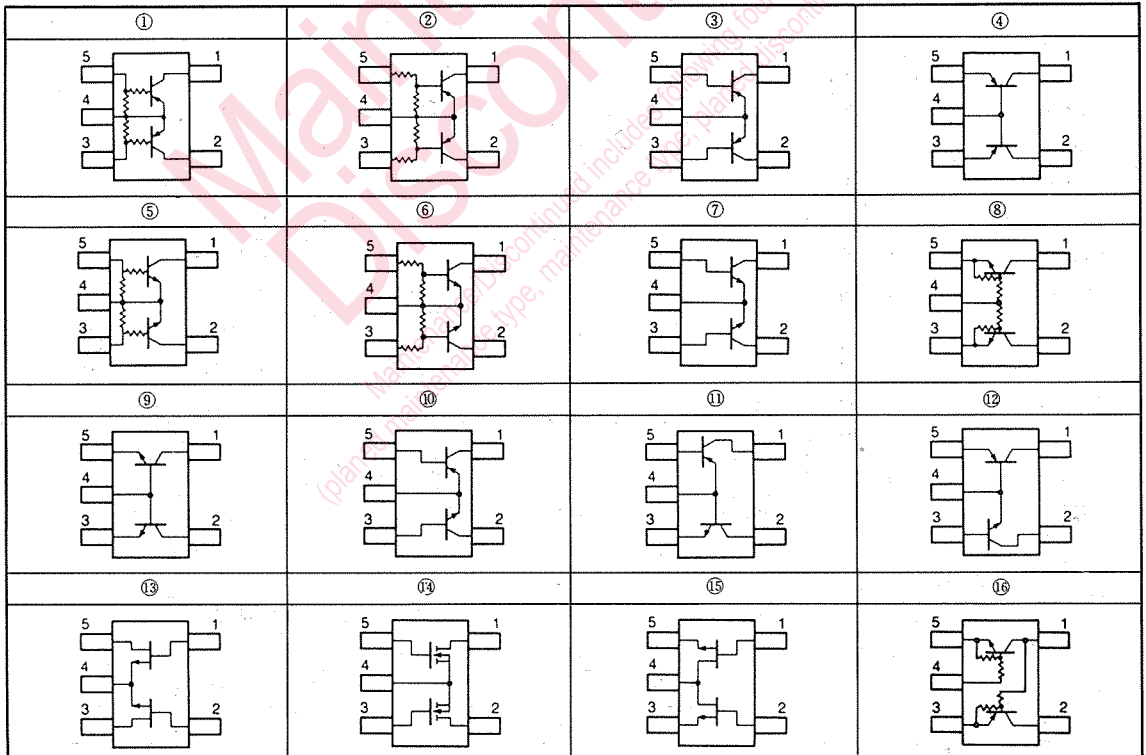
Note: A certain types are different from standard types, please check specifications for confirmation.

* : Ta=25°C

■ Package Dimensions



■ Equivalent Circuit



Main Characteristics List (Ta=25°C) (cont.)

Type No.	Details	Equivalent Circuit	Model No. Indication Number	Absolute Maximum Ratings		h _{FE}	I _C (mA)	f _T typ. (MHz)	V _{CE(sat)}		Name of Device Used (MINI 3 Devices)
				V _{CEO} (V)	I _C (mA)				typ. (V)	I _C (mA)	
XN1101	PNP × 2 PNP's	①	AH	-40	-30	80~	-5	80	-0.1	-10	UN5101 R _B =10kΩ, R _{BE} =500kΩ
XN1111		②	9S	-50	-100	35~	-5	80	-0.07	-10	UN2111 R _B =10kΩ, R _{BE} =10kΩ
XN1112		②	7K	-50	-100	60~	-5	80	-0.07	-10	UN2112 R _B =22kΩ, R _{BE} =22kΩ
XN1113		②	7L	-50	-100	80~	-5	80	-0.07	-10	UN2113 R _B =47kΩ, R _{BE} =47kΩ
XN1114		②	7Q	-50	-100	80~	-5	80	-0.07	-10	UN2114 R _B =10kΩ, R _{BE} =47kΩ
XN1115		②	7M	-50	-100	160~460	-5	80	-0.07	-10	UN2115 R _B =10kΩ, R _{BE} =∞
XN1116		②	7N	-50	-100	160~460	-5	80	-0.07	-10	UN2116 R _B =4.7kΩ, R _{BE} =∞
XN1119		②	7P	-50	-100	30~	-5	80	-0.07	-10	UN2119 R _B =1kΩ, R _{BE} =10kΩ
XN1110		②	AD	-50	-100	60~	-5	80	-0.07	-10	UN2110 R _B =47kΩ, R _{BE} =∞
XN111F		②	7O	-50	-100	30~	-5	80	-0.07	-10	UN211F R _B =4.7kΩ, R _{BE} =10kΩ
XN111H		②	9X	-50	-100	30~	-5	80	-0.07	-10	UN211H R _B =2.2kΩ, R _{BE} =10kΩ
XN1401		③	5V	-50	-100	160~460	-2	80	-0.3	-100	2SB709A
XN2401		④	7R	-50	-100	160~460	-2	80	-0.3	-100	2SB709A
XN1201		NPN × 2 PNP's	⑤	AI	40	30	80~	5	150	0.1	10
XN1210	⑥		AC	50	100	160~	5	150	0.07	10	UN2210 R _B =47kΩ, R _{BE} =∞
XN1211	⑥		9T	50	100	35~	5	150	0.07	10	UN2211 R _B =10kΩ, R _{BE} =10kΩ
XN1212	⑥		9K	50	100	60~	5	150	0.07	10	UN2212 R _B =22kΩ, R _{BE} =22kΩ
XN1213	⑥		9L	50	100	80~	5	150	0.07	10	UN2213 R _B =47kΩ, R _{BE} =47kΩ
XN1214	⑥		9H	50	100	80~	5	150	0.07	10	UN2214 R _B =10kΩ, R _{BE} =47kΩ
XN1215	⑥		9M	50	100	160~460	5	150	0.07	10	UN2215 R _B =10kΩ, R _{BE} =∞
XN1216	⑥		9N	50	100	160~460	5	150	0.07	10	UN2216 R _B =4.7kΩ, R _{BE} =∞
XN1217	⑥		9P	50	100	160~460	5	150	0.07	10	UN2217 R _B =22kΩ, R _{BE} =∞
XN1501	⑦		5R	50	100	160~460	2	150	0.3	100	2SD601A
XN1504	⑦		5S	20	300	500~2500	4	80	0.18	300	2SD1938
XN1507	⑦		4O	150	50	90~450	10	150	max.1.0	30	2SD814
XN1531	⑦		9F	10	50	75~400	5	1900	max.0.5	20	2SC3130
XN2210	⑧		9Q	5	100	160~460	5	150	0.07	10	UN2210 R _B =47kΩ, R _{BE} =∞
XN2211	⑧		9O	50	100	35~	5	150	0.07	10	UN2211 R _B =10kΩ, R _{BE} =10kΩ
XN2215	⑧		9R	5	100	160~460	5	150	0.07	10	UN2215 R _B =10kΩ, R _{BE} =∞
XN2501	⑨		5W	50	100	160~460	2	150	0.3	100	2SD601A
XN2531	⑨		9I	10	50	75~400	5	1900	max.0.5	20	2SC3130
XN1601	PNP+NPN		⑩	7S	-50/50	-100/100	160~460	-2/2	80/150	-0.3/0.3	-10/10
XN1A312		⑪	4P	-50/50	-100/100	60~	-5/5	80/150	-0.07/0.07	-10/10	UN2212 : Tr ₁ +UN2112 : Tr ₂ Tr ₁ R _B =22kΩ, R _{BE} =22kΩ Tr ₂ R _B =22kΩ, R _{BE} =22kΩ
XN1B301		⑫	4Q	-50/50	-100/100	160~460	-2/2	80/150	-0.3/0.3	-10/10	2SB709A+2SD601A
XN1C301		⑬	4R	-50/50	-100/100	160~460	-2/2	80/150	-0.3/0.3	-10/10	2SB709A+2SD601A
XN1871	N-ch × 2 PNP's	⑭	5T	V _{DS} 30	I _D 20	gm:4~(mS)	I _D :0.5	-	-	-	2SK198
XN1872		⑮	5U	V _{DS} 20	I _D 100	gm:20~(mS)	I _D :20	-	-	-	2SK621
XN1D873		⑯	0C	V _{GDS} -65	I _D 20	gm:1.8~(mS)	I _D :1.0	-	-	-	2SK1103

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